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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	24MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LCD, LVD, POR, PWM, WDT
Number of I/O	42
Program Memory Size	96KB (96K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	6K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 9x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f10wlfafa-30

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Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

RL78/L13 1. OUTLINE

Pin Count	Package	Data Flash	Fields of	Ordering Part Number
			Application ^{Note}	
64 pins	64-pin plastic LQFP	Mounted	Α	R5F10WLAAFA#30, R5F10WLAAFA#50, R5F10WLCAFA#30,
	(12 × 12 mm, 0.65			R5F10WLCAFA#50, R5F10WLDAFA#30, R5F10WLDAFA#50,
	mm pitch)			R5F10WLEAFA#30, R5F10WLEAFA#50, R5F10WLFAFA#30,
				R5F10WLFAFA#50, R5F10WLGAFA#30, R5F10WLGAFA#50
	64-pin plastic LFQFP	Mounted	Α	R5F10WLAAFB#30, R5F10WLAAFB#50, R5F10WLCAFB#30,
	(10 × 10 mm, 0.5			R5F10WLCAFB#50, R5F10WLDAFB#30, R5F10WLDAFB#50,
	mm pitch)			R5F10WLEAFB#30, R5F10WLEAFB#50, R5F10WLFAFB#30,
				R5F10WLFAFB#50, R5F10WLGAFB#30, R5F10WLGAFB#50,
			G	R5F10WLAGFB#30, R5F10WLAGFB#50, R5F10WLCGFB#30,
				R5F10WLCGFB#50, R5F10WLDGFB#30, R5F10WLDGFB#50,
				R5F10WLEGFB#30, R5F10WLEGFB#50, R5F10WLFGFB#30,
				R5F10WLFGFB#50, R5F10WLGGFB#30, R5F10WLGGFB#50
80 pins	80-pin plastic LQFP	Mounted	Α	R5F10WMAAFA#30, R5F10WMAAFA#50, R5F10WMCAFA#30,
	(14 × 14 mm, 0.65			R5F10WMCAFA#50, R5F10WMDAFA#30, R5F10WMDAFA#50,
	mm pitch)			R5F10WMEAFA#30, R5F10WMEAFA#50, R5F10WMFAFA#30,
				R5F10WMFAFA#50, R5F10WMGAFA#30, R5F10WMGAFA#50
	80-pin plastic LFQFP	Mounted	Α	R5F10WMAAFB#30, R5F10WMAAFB#50, R5F10WMCAFB#30,
	(12 × 12 mm, 0.5			R5F10WMCAFB#50, R5F10WMDAFB#30, R5F10WMDAFB#50,
	mm pitch)			R5F10WMEAFB#30, R5F10WMEAFB#50, R5F10WMFAFB#30,
				R5F10WMFAFB#50, R5F10WMGAFB#30, R5F10WMGAFB#50,
			G	R5F10WMAGFB#30, R5F10WMAGFB#50, R5F10WMCGFB#30,
				R5F10WMCGFB#50, R5F10WMDGFB#30, R5F10WMDGFB#50,
				R5F10WMEGFB#30, R5F10WMEGFB#50, R5F10WMFGFB#30,
				R5F10WMFGFB#50, R5F10WMGGFB#30, R5F10WMGGFB#50

Note For the fields of application, see Figure 1-1 Part Number, Memory Size, and Package of RL78/L13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, high	V _{OH1}	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57,	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH1} = -10.0 \text{ mA}$	V _{DD} - 1.5			V
		P70 to P77, P125 to P127, P130	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH1} = -3.0 \text{ mA}$	V _{DD} - 0.7			V
			$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH1} = -2.0 \text{ mA}$	V _{DD} - 0.6			V
			1.8 V \leq V _{DD} \leq 5.5 V, Іон1 = -1.5 mA	V _{DD} - 0.5			V
			$1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OH1} = -1.0 \text{ mA}$	V _{DD} - 0.5			V
	V _{OH2}	P20 and P21	1.6 V \leq V _{DD} \leq 5.5 V, I _{OH2} = -100 μ A	V _{DD} - 0.5			V
Output voltage, low	V _{OL1}	P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57,	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OL1} = 20 \text{ mA}$			1.3	V
		P70 to P77, P125 to P127, P130	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OL1} = 8.5 \text{ mA}$			0.7	V
			$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $\text{I}_{OL1} = 3.0 \text{ mA}$			0.6	V
			$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OL1} = 1.5 \text{ mA}$			0.4	V
			$1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OL1} = 0.6 \text{ mA}$			0.4	V
			$1.6 \text{ V} \le \text{V}_{DD} < 1.8 \text{ V},$ $I_{OL1} = 0.3 \text{ mA}$			0.4	V
	V _{OL2}	P20 and P21	$1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OL2} = 400 \ \mu\text{A}$			0.4	V
	Vol3	P60 and P61	$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OL3} = 15.0 \text{ mA}$			2.0	V
			$4.0 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OL3} = 5.0 \text{ mA}$			0.4	V
			$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $\text{I}_{OL3} = 3.0 \text{ mA}$			0.4	V
			$1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V},$ $I_{OL3} = 2.0 \text{ mA}$			0.4	V
			1.6 V ≤ V _{DD} < 1.8 V, I _{OL3} = 1.0 mA			0.4	V

Caution P00, P04 to P07, P16, P17, P35, P42 to P44, P46, P47, P53 to P56, and P130 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

- Notes 1. Total current flowing into V_{DD}, including the input leakage current flowing when the level of the input pin is fixed to V_{DD} or V_{SS}. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the LCD controller/driver, A/D converter, LVD circuit, comparator, I/O port, on-chip pull-up/pull-down resistors, and the current flowing during data flash rewrite.
 - 2. When high-speed on-chip oscillator and subsystem clock are stopped.
 - 3. When high-speed system clock and subsystem clock are stopped.
 - **4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When setting ultra-low power consumption oscillation (AMPHS1 = 1). The current flowing into the LCD controller/driver, 16-bit timer KB20, real-time clock 2, 12-bit interval timer, and watchdog timer is not included.
 - 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} @1 \text{ MHz}$ to 24 MHz

 $2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V@1 MHz to 16 MHz}$

LS (low-speed main) mode: $1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} \textcircled{2}1 \text{ MHz to } 8 \text{ MHz}$ LV (low-voltage main) mode: $1.6 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V} \textcircled{2}1 \text{ MHz to } 4 \text{ MHz}$

- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fHoco: High-speed on-chip oscillator clock frequency (48 MHz max.)
 - 3. fil: High-speed on-chip oscillator clock frequency (24 MHz max.)
 - 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Condition	ns		MIN.	TYP.	MAX.	Unit
Low-speed on- chip oscillator operating current	_{FIL} Note 1		four = 32 768 kHz						μΑ
RTC2 operating current	I _{RTC} Notes 1, 2,	f _{SUB} = 32.768 kHz					0.02		μΑ
12-bit interval timer operating current	I _{TMKA} Notes 1, 2,						0.04		μΑ
Watchdog timer operating current	_{WDT} Notes 1, 2, 5	f∟ = 15 kHz					0.22		μΑ
A/D converter operating current	ADC ^{Notes 1, 6}	When conversion at maximum speed	Normal mode	·	$_{D} = 5.0 \text{ V}$ = $V_{DD} = 3.0 \text{ V}$		1.3 0.5	1.7 0.7	mA mA
A/D converter reference voltage current	ADREFNote 1						75.0		μΑ
Temperature sensor operating current	TMPS Note 1						75.0		μА
LVD operating current	_{LVD} Notes 1, 7						0.08		μΑ
Comparator	ICMPNotes 1, 11	V _{DD} = 5.0 V,	Window mode	е			12.5		μΑ
operating current		Regulator output	Comparator h	nigh-speed mo	ode		6.5		μΑ
		voltage = 2.1 V	Comparator low-speed mode				1.7		μΑ
		V _{DD} = 5.0 V,	Window mode				8.0		μΑ
		Regulator output voltage = 1.8 V	Comparator high-speed mode				4.0		μΑ
		Voltage = 1.6 V	Comparator lo	ow-speed mo	de		1.3		μΑ
Self- programming operating current	FSP ^{Notes 1, 9}						2.00	12.20	mA
BGO operating current	BGO ^{Notes 1, 8}						2.00	12.20	mA
SNOOZE	ISNOZ ^{Note 1}	ADC operation	While the mod	de is shifting ^N	ote 10		0.50	0.60	mA
operating current			During A/D co		•		1.20	1.44	mA
		CSI/UART operation	1				0.70	0.84	mA
LCD operating current		External resistance division method	fLCD = fSUB LCD clock = 128 Hz	1/3 bias, four time slices	V _{DD} = 5.0 V, V _{L4} = 5.0 V		0.04	0.20	μА
		Internal voltage boosting method	fLCD = fSUB LCD clock = 128 Hz	1/3 bias, four time slices	$V_{DD} = 3.0 \text{ V},$ $V_{L4} = 3.0 \text{ V}$ $(V_{LCD} = 04\text{H})$		0.85	2.20	μΑ
					$V_{DD} = 5.0 \text{ V},$ $V_{L4} = 5.1 \text{ V}$ $(V_{LCD} = 12\text{H})$		1.55	3.70	μΑ
ILCD3 ^{Note 1, 12}		Capacitor split method	fLCD = fSUB LCD clock = 128 Hz	1/3 bias, four time slices	V _{DD} = 3.0 V, V _{L4} = 3.0 V		0.20	0.50	μΑ

(Notes and Remarks are listed on the next page.)



2.4 AC Characteristics

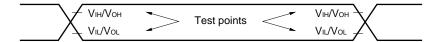
(TA = -40 to +85°C, 1.6 V \leq VDD \leq 5.5 V, Vss = 0 V)

Parameter	Symbol		Conditions		MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Tcy	Main system	HS (high-speed	$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	0.0417		1	μs
instruction execution time)		clock (fmain)	main) mode	2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
		operation	LS (low-speed main) mode	1.8 V ≤ V _{DD} ≤ 5.5 V	0.125		1	μs
			LV (low-voltage main) mode	1.6 V ≤ V _{DD} ≤ 5.5 V	0.25		1	μs
		Subsystem clo	ock (fsuв)	$1.8 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$	28.5	30.5	31.3	μs
		In the self	HS (high-speed	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	0.0417		1	μs
		programming mode	main) mode	2.4 V ≤ V _{DD} < 2.7 V	0.0625		1	μs
		mode	LS (low-speed main) mode	$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	0.125		1	μs
			LV (low-voltage main) mode	$1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	0.25		1	μs
External system clock	fex	2.7 V ≤ V _{DD} ≤	5.5 V	•	1.0		20.0	MHz
frequency		2.4 V ≤ V _{DD} <	2.7 V		1.0		16.0	MHz
		1.8 V ≤ V _{DD} <	2.4 V		1.0		8.0	MHz
		1.6 V ≤ V _{DD} <	1.8 V		1.0		4.0	MHz
	fexs				32		35	kHz
External system clock input	texH,	2.7 V ≤ V _{DD} ≤	5.5 V		24			ns
high-level width, low-level width	t EXL	2.4 V ≤ V _{DD} <	2.7 V		30			ns
wiath		1.8 V ≤ V _{DD} <	2.4 V		60			ns
		1.6 V ≤ V _{DD} <	1.8 V		120			ns
	texhs, texhs				13.7			μs
TI00 to TI07 input high-level width, low-level width	tтін, tтіL				1/fмск+10			ns
TO00 to TO07, TKBO00,	fто	HS (high-spee	ed main) mode	$4.0~V \leq V_{DD} \leq 5.5~V$			12	MHz
TKBO01-0 to TKBO01-2 output frequency				$2.7 \text{ V} \le V_{DD} \le 4.0 \text{ V}$			8	MHz
output frequency				$2.4 \text{ V} \leq V_{DD} \leq 2.7 \text{ V}$			4	MHz
		LV (low-voltag	ge main) mode	$1.6~V \leq V_{DD} \leq 5.5~V$			2	MHz
		LS (low-speed	d main) mode	$1.8~V \leq V_{DD} \leq 5.5~V$			4	MHz
PCLBUZ0, PCLBUZ1 output	f PCL	HS (high-spee	ed main) mode	$4.0 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$			16	MHz
frequency				$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			8	MHz
				$2.4 \text{ V} \le \text{V}_{DD} \le 2.7 \text{ V}$			4	MHz
		LV (low-voltag	ge main) mode	$1.8~V \leq V_{DD} \leq 5.5~V$			4	MHz
				1.6 V ≤ V _{DD} < 1.8 V			2	MHz
		LS (low-speed	d main) mode	$1.8~V \leq V_{DD} \leq 5.5~V$			4	MHz
Interrupt input high-level width, low-level width	tinth, tintl	INTP0 to INTF	27	$1.6~V \le V_{DD} \le 5.5~V$	1			μs
Key interrupt input high-level	tkrh, tkrl	KR0 to KR7		$1.8~V \leq V_{\text{DD}} \leq 5.5~V$	250			ns
width, low-level width				$1.6 \text{ V} \le \text{V}_{DD} \le 1.8 \text{ V}$	1			μs
IH-PWM output restart input high-level width	tihr	INTP0 to INTF	27		2			fclk
TMKB2 forced output stop	t IHR	INTP0 to INTF	22		2			fclk
input high-level width								

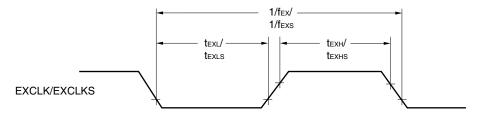
(Note and Remark are listed on the next page.)



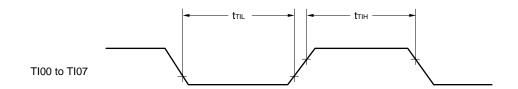
AC Timing Test Points

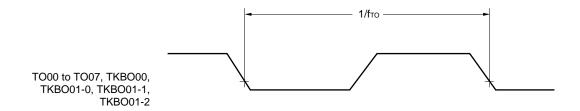


External System Clock Timing

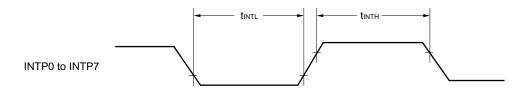


TI/TO Timing





Interrupt Request Input Timing



(5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode) (1/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol			Conditions		h-speed Mode		v-speed Mode	LV (low-voltage main) Mode		Unit
						MAX.	MIN.	MAX.	MIN.	MAX.	
Transfer rate		Reception	$\begin{array}{c c} & 4.0 \ V \leq V_{DD} \leq 5.5 \ V, \\ & 2.7 \ V \leq V_{b} \leq 4.0 \ V \end{array}$			fmck/6 ^{Note}		fмск/6 ^{Note} 1		fмск/6 ^{Note} 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note 3}$		4.0		1.3		0.6	Mbps
				$V \le V_{DD} < 4.0 \text{ V},$ $V \le V_{b} \le 2.7 \text{ V}$		fmck/6 ^{Note}		fмск/6 ^{Note} 1		fмск/6 ^{Note} 1	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note \ 3}$		4.0		1.3		0.6	Mbps
			V,	$3 \text{ V } (2.4 \text{ V}^{\text{Note 4}}) \le \text{V}_{\text{DD}} < 3.3$ $3 \text{ V } \le \text{V}_{\text{b}} \le 2.0 \text{ V}$		fMCK/6 Note s1, 2		fMCK/6 Notes 1, 2		fMCK/6 Notes 1, 2	bps
				Theoretical value of the maximum transfer rate $f_{MCK} = f_{CLK}^{Note \ 3}$		4.0		1.3		0.6	Mbps

Notes 1. Transfer rate in SNOOZE mode is 4800 bps only.

2. Use it with $V_{DD} \ge V_b$.

3. The maximum operating frequencies of the CPU/peripheral hardware clock (fclk) are:

HS (high-speed main) mode: 24 MHz (2.7 V \leq V_{DD} \leq 5.5 V)

16 MHz (2.4 V \leq V_{DD} \leq 5.5 V)

LS (low-speed main) mode: 8 MHz (1.8 V \leq VDD \leq 5.5 V) LV (low-voltage main) mode: 4 MHz (1.6 V \leq VDD \leq 5.5 V)

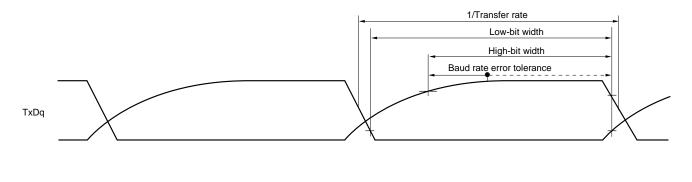
4. Condition in the HS (high-speed main) mode

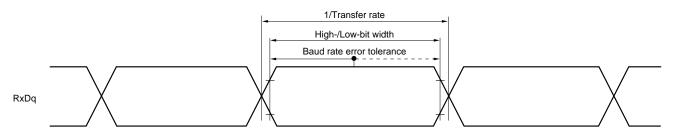
Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (Vpd tolerance) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For Vih and Vil, see the DC characteristics with TTL input buffer selected.

Remarks 1. V_b[V]: Communication line voltage

- 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 3)
- 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

UART mode bit width (during communication at different potential) (reference)





- Remarks 1. $R_b[\Omega]$: Communication line (TxDq) pull-up resistance, $C_b[F]$: Communication line (TxDq) load capacitance, $V_b[V]$: Communication line voltage
 - 2. q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 3)
 - 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))

(6) Communication at different potential (2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output, corresponding CSI00 only)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.7 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (high	h-speed Mode	,	/-speed Mode	LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tксү1	tkcy1 ≥ 2/fcLk	$ 4.0 \ V \leq V_{DD} \leq 5.5 \ V, $ $ 2.7 \ V \leq V_b \leq 4.0 \ V, $ $ C_b = 20 \ pF, \ R_b = 1.4 \ k\Omega $	200		1150		1150		ns
			$ 2.7 \text{ V} \leq \text{V}_{DD} < 4.0 \text{ V}, \\ 2.3 \text{ V} \leq \text{V}_{b} \leq 2.7 \text{ V}, \\ C_{b} = 20 \text{ pF}, R_{b} = 2.7 \text{ k}\Omega $	300		1150		1150		ns
SCKp high-level width	t кн1	$\begin{split} 4.0 \; V &\leq V_{DD} \leq 5.5 \; V, \; 2.7 \; V \leq V_b \leq 4.0 \; V, \\ C_b &= 20 \; pF, \; R_b = 1.4 \; k\Omega \end{split}$		tkcy1/2 – 50		tксү1/2 — 50		txcy1/2 - 50		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b = 1.$	0 V, 2.3 V \leq V _b \leq 2.7 V, = 2.7 kΩ	tkcy1/2 - 120		tксү1/2 — 120		tkcy1/2 - 120		ns
SCKp low-level width	t KL1	$4.0 \text{ V} \le \text{V}_{DD} \le 5$ $C_b = 20 \text{ pF}, R_b = 100 \text{ pF}$.5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 kΩ	tkcy1/2 –		tксү1/2 — 50		tксү1/2 — 50		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b = 1.$	0 V, 2.3 V \leq V _b \leq 2.7 V, = 2.7 kΩ	tkcy1/2 – 10		tксү1/2 — 50		tксү1/2 — 50		ns
SIp setup time (to SCKp↑) ^{Note 1}	tsıĸı	$4.0 \text{ V} \le \text{V}_{DD} \le 5$ $C_b = 20 \text{ pF}, R_b = 100 \text{ pF}$.5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 kΩ	58		479		479		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b = 1.$	0 V, 2.3 V \leq V _b \leq 2.7 V, = 2.7 kΩ	121		479		479		ns
SIp hold time (from SCKp↑) ^{Note}	tksi1	$4.0 \text{ V} \le \text{V}_{DD} \le 5$ $C_b = 20 \text{ pF}, R_b = 100 \text{ pF}$.5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 kΩ	10		10		10		ns
1		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b = 1.$	0 V, 2.3 V \leq V _b \leq 2.7 V, = 2.7 kΩ	10		10		10		ns
Delay time from SCKp↓ to	tkso1	$4.0 \text{ V} \le \text{V}_{DD} \le 5$ $C_b = 20 \text{ pF}, R_b = 100 \text{ pF}$.5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 kΩ		60		60		60	ns
SOp output ^{Note 1}		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b = 1.$	0 V, 2.3 V \leq V _b \leq 2.7 V, = 2.7 kΩ		130		130		130	ns
SIp setup time (to SCKp↓) ^{Note 2}	tsıĸ1	$4.0 \text{ V} \le \text{V}_{DD} \le 5$ $C_b = 20 \text{ pF}, R_b = 100 \text{ pF}$.5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 kΩ	23		110		110		ns
		$2.7 \text{ V} \le \text{V}_{DD} < 4.$ $C_b = 20 \text{ pF}, R_b = 1.$	0 V, 2.3 V \leq V _b \leq 2.7 V, = 2.7 kΩ	33		110		110		ns
SIp hold time (from SCKp↓) ^{Note}	t KSI1	$4.0 \text{ V} \le \text{V}_{DD} \le 5$ $C_b = 20 \text{ pF}, R_b = 100 \text{ pF}$.5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 kΩ	10		10		10		ns
2		2.7 V ≤ V _{DD} < 4. C _b = 20 pF, R _b	0 V, 2.3 V \leq V _b \leq 2.7 V, = 2.7 kΩ	10		10		10		ns
Delay time from SCKp↑ to	tkso1	$4.0 \text{ V} \le \text{V}_{DD} \le 5$ $C_b = 20 \text{ pF}, R_b = 100 \text{ pF}$.5 V, 2.7 V \leq V _b \leq 4.0 V, = 1.4 kΩ		10		10		10	ns
SOp output ^{Note 2}		2.7 V ≤ V _{DD} < 4. C _b = 20 pF, R _b	0 V, 2.3 V \leq V _b \leq 2.7 V, = 2.7 kΩ		10		10		10	ns

(Notes, Caution and Remarks are listed on the next page.)

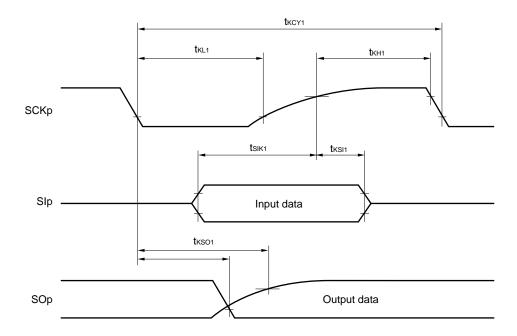


- Notes 1. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.
 - 2. When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
- Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.
- **Remarks 1.** R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage
 - 2. p: CSI number (p = 00), m: Unit number (m = 0), n: Channel number (n = 0),g: PIM and POM number (g = 1)
 - 3. fmck: Serial array unit operation clock frequency

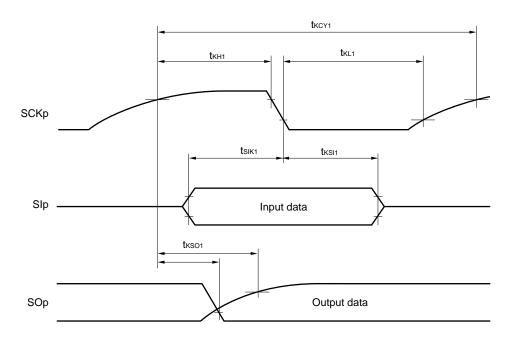
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00))
 - 4. This specification is valid only when CSI00's peripheral I/O redirect function is not used.

RENESAS

CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



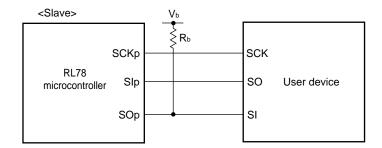
Remarks 1. R_b[Ω]: Communication line (SCKp, SOp) pull-up resistance, C_b[F]: Communication line (SCKp, SOp) load capacitance, V_b[V]: Communication line voltage

- 2. p: CSI number (p = 00, 10), m: Unit number, n: Channel number (mn = 00, 02), g: PIM and POM number (g = 0, 1)
- fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00)

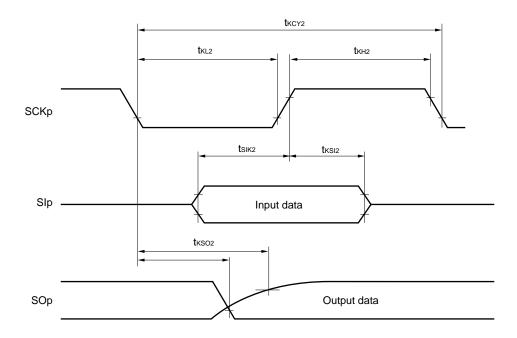
- Notes 1. Transfer rate in SNOOZE mode: MAX. 1 Mbps
 - 2. Condition in HS (high-speed main) mode
 - 3. Use it with $V_{DD} \ge V_b$.
 - **4.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **5.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **6.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.

Caution Select the TTL input buffer for the SIp pin and SCKp pin and the N-ch open drain output (VDD tolerance) mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

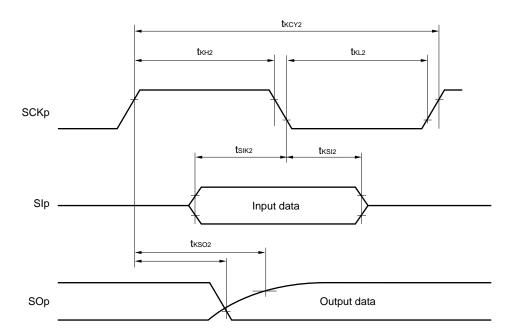
CSI mode connection diagram (during communication at different potential)



CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (slave mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. $R_b[\Omega]$: Communication line (SOp) pull-up resistance, $C_b[F]$: Communication line (SOp) load capacitance, $V_b[V]$: Communication line voltage

- 2. p: CSI number (p = 00, 10), m: Unit number, n: Channel number (mn = 00, 02), g: PIM and POM number (g = 0, 1)
- 3. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn) m: Unit number, n: Channel number (mn = 00, 02))

2.7.2 Internal voltage boosting method

(1) 1/3 bias method

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Cond	litions	MIN.	TYP.	MAX.	Unit
LCD output voltage variation range	V _{L1}	C1 to C4 ^{Note 1}	VLCD = 04H	0.90	1.00	1.08	V
		= 0.47 μ F ^{Note 2}	VLCD = 05H	0.95	1.05	1.13	V
			VLCD = 06H	1.00	1.10	1.18	V
			VLCD = 07H	1.05	1.15	1.23	V
			VLCD = 08H	1.10	1.20	1.28	V
			VLCD = 09H	1.15	1.25	1.33	V
			VLCD = 0AH	1.20	1.30	1.38	V
			VLCD = 0BH	1.25	1.35	1.43	V
			VLCD = 0CH	1.30	1.40	1.48	V
			VLCD = 0DH	1.35	1.45	1.53	V
			VLCD = 0EH	1.40	1.50	1.58	V
			VLCD = 0FH	1.45	1.55	1.63	V
			VLCD = 10H	1.50	1.60	1.68	V
			VLCD = 11H	1.55	1.65	1.73	V
			VLCD = 12H	1.60	1.70	1.78	V
			VLCD = 13H	1.65	1.75	1.83	V
Doubler output voltage	V _{L2}	C1 to C4 ^{Note 1} =	0.47 μF	2 V _{L1} – 0.10	2 V _{L1}	2 V _{L1}	V
Tripler output voltage	V _{L4}	C1 to C4 ^{Note 1} =	0.47 <i>μ</i> F	3 VL1 – 0.15	3 V _{L1}	3 V _{L1}	V
Reference voltage setup time ^{Note 2}	tvwait1			5			ms
Voltage boost wait timeNote 3	tvwait2	C1 to C4 ^{Note 1} =	0.47 μF	500			ms

Notes 1. This is a capacitor that is connected between voltage pins used to drive the LCD.

- C1: A capacitor connected between CAPH and CAPL
- C2: A capacitor connected between V_{L1} and GND
- C3: A capacitor connected between V_{L2} and GND
- C4: A capacitor connected between V_{L4} and GND
- C1 = C2 = C3 = C4 = 0.47 μ F \pm 30 %
- 2. This is the time required to wait from when the reference voltage is specified by using the VLCD register (or when the internal voltage boosting method is selected (by setting the MDSET1 and MDSET0 bits of the LCDM0 register to 01B) if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).
- 3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).

(2) 1/4 bias method

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Cor	nditions	MIN.	TYP.	MAX.	Unit
LCD output voltage variation range	V _{L1}	C1 to C5 ^{Note 1}	VLCD = 04H	0.90	1.00	1.08	V
		= 0.47 μ F ^{Note 2}	VLCD = 05H	0.95	1.05	1.13	V
			VLCD = 06H	1.00	1.10	1.18	٧
			VLCD = 07H	1.05	1.15	1.23	V
			VLCD = 08H	1.10	1.20	1.28	V
			VLCD = 09H	1.15	1.25	1.33	V
			VLCD = 0AH	1.20	1.30	1.38	V
Doubler output voltage	V _{L2}	C1 to C5 ^{Note 1} =	0.47 <i>μ</i> F	2 V _{L1} -0.08	2 V _{L1}	2 V _{L1}	V
Tripler output voltage	V _{L3}	C1 to C5 ^{Note 1} =	0.47 <i>μ</i> F	3 VL1-0.12	3 VL1	3 V _{L1}	V
Quadruply output voltage	V _{L4}	C1 to C5 ^{Note 1} =	0.47 <i>μ</i> F	4 VL1-0.16	4 V _{L1}	4 V _{L1}	V
Reference voltage setup timeNote 2	tvwait1			5			ms
Voltage boost wait timeNote 3	tvwait2	C1 to C5 ^{Note 1} =	0.47 <i>μ</i> F	500			ms

Notes 1. This is a capacitor that is connected between voltage pins used to drive the LCD.

- C1: A capacitor connected between CAPH and CAPL
- C2: A capacitor connected between V_{L1} and GND
- C3: A capacitor connected between V_{L2} and GND
- C4: A capacitor connected between VL3 and GND
- C5: A capacitor connected between V_{L4} and GND
- C1 = C2 = C3 = C4 = C5 = 0.47 μ F \pm 30%
- 2. This is the time required to wait from when the reference voltage is specified by using the VLCD register (or when the internal voltage boosting method is selected (by setting the MDSET1 and MDSET0 bits of the LCDM0 register to 01B) if the default value reference voltage is used) until voltage boosting starts (VLCON = 1).
- 3. This is the wait time from when voltage boosting is started (VLCON = 1) until display is enabled (LCDON = 1).

2.7.3 Capacitor split method

(1) 1/3 bias method

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 2.2 \text{ V} \le V_D \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
V _{L4} voltage	V _{L4}	C1 to C4 = 0.47 µF ^{Note 2}		V _{DD}		V
V _{L2} voltage	V _{L2}	C1 to C4 = 0.47 μ F ^{Note 2}	2/3 V _{L4} – 0.1	2/3 V _{L4}	2/3 V _{L4} + 0.1	V
V _{L1} voltage	V _{L1}	C1 to C4 = 0.47 μ F ^{Note 2}	1/3 V _{L4} – 0.1	1/3 V _{L4}	1/3 V _{L4} + 0.1	V
Capacitor split wait timeNote 1	tvwait		100			ms

Notes 1. This is the wait time from when voltage bucking is started (VLCON = 1) until display is enabled (LCDON = 1).

- 2. This is a capacitor that is connected between voltage pins used to drive the LCD.
 - C1: A capacitor connected between CAPH and CAPL
 - C2: A capacitor connected between V_{L1} and GND
 - C3: A capacitor connected between VL2 and GND
 - C4: A capacitor connected between VL4 and GND
 - C1 = C2 = C3 = C4 = 0.47 μ F \pm 30%

3.3 DC Characteristics

3.3.1 Pin characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{ Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output current, high ^{Note 1}	І он1	Per pin for P00 to P07, P10 to P17, P22 to P27, P30 to P35, P40 to P47, P50 to P57, P70 to P77, P125 to P127, P130	2.4 V ≤ V _{DD} ≤ 5.5 V			-3.0 ^{Note 2}	mA
		Total of P00 to P07, P10 to P17,	$4.0~V \leq V_{DD} \leq 5.5~V$			-45.0	mA
		P22 to P27, P30 to P35, P40 to P47, P50	$2.7 \text{ V} \le \text{V}_{DD} \le 4.0 \text{ V}$			-15.0	mA
		to P57, P70 to P77, P125 to P127, P130 (When duty = 70% ^{Note 3})	$2.4 \text{ V} \le \text{V}_{DD} \le 2.7 \text{ V}$			-7.0	mA
	І он2	Per pin for P20 and P21	$2.4~V \leq V_{DD} \leq 5.5~V$			-0.1 ^{Note 2}	mA
		Total of all pins (When duty = 70% ^{Note 3})	$2.4~V \le V_{DD} \le 5.5~V$			-0.2	mA

Notes 1. Value of the current at which the device operation is guaranteed even if the current flows from the V_{DD} pin to an output pin

- 2. Do not exceed the total current value.
- 3. Output current value under conditions where the duty factor $\leq 70\%$.

The output current value that has changed to the duty factor > 70% the duty ratio can be calculated with the following expression (when changing the duty factor from 70% to n%).

- Total output current of pins = (IoH × 0.7)/(n × 0.01)
- <Example> Where n = 80% and IoH = -45.0 mA

Total output current of pins = $(-45.0 \times 0.7)/(80 \times 0.01) = -39.375$ mA

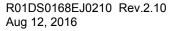
However, the current that is allowed to flow into one pin does not vary depending on the duty factor. A current higher than the absolute maximum rating must not flow into one pin.

Caution P00, P04 to P07, P16, P17, P35, P42 to P44, P46, P47, P53 to P56, and P130 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.



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3.3.2 Supply current characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

(1/2)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	I _{DD1} Note 1	Operating	HS (high-	f _{HOCO} = 48 MHz ^{Note}	Basic	V _{DD} = 5.0 V		2.0		mA
current		mode	speed main)	3,	operation	V _{DD} = 3.0 V		2.0		mA
			mode ^{Note 5}	f _{IH} = 24 MHz ^{Note 3}	Normal	V _{DD} = 5.0 V		3.8	7.0	mA
					operation	V _{DD} = 3.0 V		3.8	7.0	mA
				f _{HOCO} = 24 MHz ^{Note}	Basic	V _{DD} = 5.0 V		1.7		mA
				3,	operation	V _{DD} = 3.0 V		1.7		mA
				f _{IH} = 24 MHz ^{Note 3}	Normal	V _{DD} = 5.0 V		3.6	6.5	mA
					operation	V _{DD} = 3.0 V		3.6	6.5	mA
				f _{HOCO} = 16 MHz ^{Note}	Normal	V _{DD} = 5.0 V		2.7	5.0	mA
				³ , f _{IH} = 16 MHz ^{Note 3}	operation	V _{DD} = 3.0 V		2.7	5.0	mA
			HS (high-	f _{MX} = 20 MHz ^{Note 2} ,	Normal	Square wave input		3.0	5.4	mA
			speed main)	V _{DD} = 5.0 V	operation	Resonator connection		3.2	5.6	mA
				f _{MX} = 20 MHz ^{Note 2} ,	Nomal	Square wave input		2.9	5.4	mA
		V _{DD} = 3.0 V	operation	Resonator connection		3.2	5.6	mA		
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		1.9	3.2	mA
		V _{DD} = 5.0 V	operation	Resonator connection		1.9	3.2	mA		
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Nomal	Square wave input		1.9	3.2	mA
				V _{DD} = 3.0 V	operation	Resonator connection		1.9	3.2	mA
			Subsystem	f _{SUB} =	Nomal	Square wave input		4.0	5.4	μΑ
			clock operation	32.768 kHz ^{Note 4} , $T_A = -40^{\circ}C$	operation	Resonator connection		4.3	5.4	μΑ
				fsub =	Normal	Square wave input		4.0	5.4	μΑ
				32.768 kHz Note 4, T _A = +25°C	operation	Resonator connection		4.3	5.4	μΑ
				f _{SUB} =	Nomal	Square wave input		4.1	7.1	μΑ
				32.768 kHz ^{Note 4} , T _A = +50°C	operation	Resonator connection		4.4	7.1	μΑ
				f _{SUB} =	Nomal	Square wave input		4.3	8.7	μΑ
				32.768 kHz ^{Note 4} , T _A = +70°C	operation	Resonator connection		4.7	8.7	μΑ
			f _{SUB} =	Nomal	Square wave input		4.7	12.0	μΑ	
			32.768 kHz ^{Note 4} , T _A = +85°C	operation	Resonator connection		5.2	12.0	μΑ	
				f _{SUB} =	Nomal	Square wave input		6.4	35.0	μΑ
				32.768 kHz ^{Note 4} , T _A = +105°C	operation	Resonator connection		6.6	35.0	μΑ

(Notes and Remarks are listed on the next page.)



(2) During communication at same potential (CSI mode) (master mode, SCKp... internal clock output) $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol	Conditions	HS (high-speed main) Mode		Unit
			MIN.	MAX.	-
SCKp cycle time	tkcy1	$2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}$	334 ^{Note 1}		ns
		2.4 V ≤ V _{DD} ≤ 5.5 V	500 ^{Note 1}		ns
SCKp high-/low-level width	t кн1,	$4.0 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	tkcy1/2 - 24		ns
	t _{KL1}	$2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}$	tkcy1/2 - 36		ns
		$2.4 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$	tkcy1/2 - 76		ns
SIp setup time (to SCKp↑) ^{Note 2}	tsıĸ1	$4.0 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	66		ns
		$2.7 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$	66		ns
		$2.4 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}$	113		ns
SIp hold time (from SCKp↑)Note 3	t _{KSI1}		38		ns
Delay time from SCKp↓ to SOp output ^{Note 4}	tkso1	C = 30 pF ^{Note 5}		50	ns

- Notes 1. The value must also be equal to or more than 4/fclk.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp \downarrow " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - **4.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 5. C is the load capacitance of the SCKp and SOp output lines.

Caution Select the normal input buffer for the SIp pin and the normal output mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

Remarks 1. p: CSI number (p = 00, 10), m: Unit number (m = 0), n: Channel number (n = 0, 2), g: PIM and POM numbers (g = 0, 1)

2. fmck: Serial array unit operation clock frequency (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00, 02))



(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/2) $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \leq V_{DD} \leq 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Symbol		Conditions	HS (high-speed main) Mode		Unit
					MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fclk	$ \begin{aligned} 4.0 & \ V \le V_{DD} \le 5.5 \ V, \\ 2.7 & \ V \le V_b \le 4.0 \ V, \\ C_b & = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{aligned} $	600		ns
			$ \begin{aligned} &2.7 \; V \leq V_{DD} < 4.0 \; V, \\ &2.3 \; V \leq V_b \leq 2.7 \; V, \\ &C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{aligned} $	1000		ns
			$2.4 \ V \leq V_{DD} < 3.3 \ V,$ $1.6 \ V \leq V_b \leq 1.8 \ V,$ $C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega$	2300		ns
SCKp high-level width	tкн1	$ 4.0 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V}, \ 2.7 \text{ V} \leq \text{V}_{\text{b}} \leq 4.0 \text{ V}, $ $ C_{\text{b}} = 30 \text{ pF}, \ R_{\text{b}} = 1.4 \text{ k}\Omega $		tkcy1/2 – 150		ns
		$2.7 \; V \leq V_{DD} < 4.0 \; V, 2.3 \; V \leq V_b \leq 2.7 \; V,$ $C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega$		tксү1/2 - 340		ns
		$2.4 \ V \leq V_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V,$ $C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega$		tkcy1/2 - 916		ns
SCKp low-level width	t KL1	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF, F}$	$6.5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $R_b = 1.4 \text{ k}\Omega$	tксү1/2 – 24		ns
		$2.7 \text{ V} \leq \text{V}_{DD} \leq \text{C}_{b} = 30 \text{ pF, F}$	$= 4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $= 2.7 \text{ k}Ω$	tксү1/2 – 36		ns
		$2.4 \ V \leq V_{DD} < 3.3 \ V, \ 1.6 \ V \leq V_b \leq 2.0 \ V,$ $C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega$		tkcy1/2 - 100		ns
SIp setup time (to SCKp↑) ^{Note 1}	t sıĸı	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$6.5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $R_b = 1.4 \text{ k}\Omega$	162		ns
		$2.7 \text{ V} \leq \text{V}_{DD} \leq$ $C_b = 30 \text{ pF, F}$	$4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $R_b = 2.7 \text{ k}\Omega$	354		ns
		$ 2.4 \text{ V} \leq \text{V}_{\text{DD}} < 3.3 \text{ V}, \ 1.6 \text{ V} \leq \text{V}_{\text{b}} \leq 2.0 \text{ V}, \\ C_{\text{b}} = 30 \text{ pF}, \ R_{\text{b}} = 5.5 \text{ k}\Omega $		958		ns
SIp hold time triple (from SCKp↑)Note 1	t ksii	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$6.5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $R_b = 1.4 \text{ k}\Omega$	38		ns
		$2.7 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$4.0 \text{ V}, 2.3 \text{ V} \le \text{V}_b \le 2.7 \text{ V},$ $R_b = 2.7 \text{ k}\Omega$	38		ns
		$2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq C_{\text{b}} = 30 \text{ pF, F}$	$3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_b \le 2.0 \text{ V},$ $R_b = 5.5 \text{ k}\Omega$	38		ns
Delay time from SCKp↓ to SOp output ^{Note 1}	tkso1	$4.0 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$6.5.5 \text{ V}, 2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V},$ $R_b = 1.4 \text{ k}\Omega$		200	ns
		$ 2.7 \; V \leq V_{DD} < 4.0 \; V, \; 2.3 \; V \leq V_b \leq 2.7 \; V, $ $ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega $			390	ns
		$2.4 \text{ V} \le \text{V}_{DD} \le C_b = 30 \text{ pF}, \text{ F}$	$3.3 \text{ V}, 1.6 \text{ V} \le \text{V}_b \le 2.0 \text{ V},$ $R_b = 5.5 \text{ k}\Omega$		966	ns

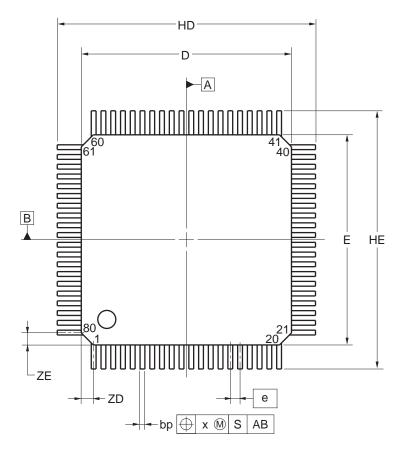
(Note, ${\bf Caution}$ and ${\bf Remark}$ are listed on the next page.)

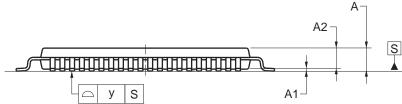


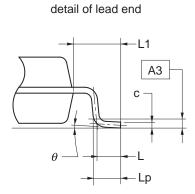
4.2 80-pin Products

R5F10WMAAFA, R5F10WMCAFA, R5F10WMDAFA, R5F10WMEAFA, R5F10WMFAFA, R5F10WMGAFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP80-14x14-0.65	PLQP0080JB-E	P80GC-65-UBT-2	0.69







Referance	Dimension in Millimeters				
Symbol	Min	Nom	Max		
D	13.80	14.00	14.20		
Е	13.80	14.00	14.20		
HD	17.00	17.20	17.40		
HE	17.00	17.20	17.40		
Α			1.70		
A1	0.05	0.125	0.20		
A2	1.35	1.40	1.45		
A3	—	0.25			
bp	0.26	0.32	0.38		
С	0.10	0.145	0.20		
L		0.80			
Lp	0.736	0.886	1.036		
L1	1.40	1.60	1.80		
	0°	3°	8°		
е		0.65			
х			0.13		
У			0.10		
ZD		0.825			
ZE		0.825			